



MRF837

NPN SILICON RF LOW POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF837** is Designed primarily for wideband large signal predriver stages in 800 MHz and UHF frequency ranges.

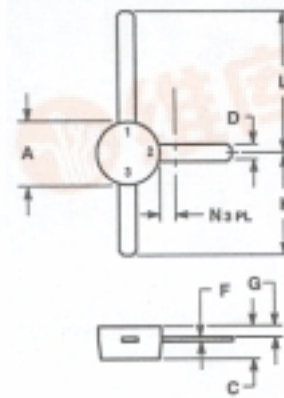
FEATURES INCLUDE:

- Min gain 8.0 dB @ 750 mW/870 MHz
- Silicon Nitride passivated
- Low cost Plastic Package

MAXIMUM RATINGS

I_C	200 mA
V_{CB0}	36 V
P_{DISS}	1.0 W @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	40 °C/W

PACKAGE STYLE MACRO-X



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.44	5.21	0.175	0.205
C	1.90	2.54	0.075	0.100
D	0.84	0.99	0.033	0.039
F	0.20	0.30	0.008	0.012
G	0.76	0.14	0.030	0.045
K	7.24	8.13	0.285	0.320
L	10.54	11.43	0.415	0.450
N	---	1.65	---	0.065

1 = COLLECTOR 2 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 5.0 mA	36			V
BV_{CEO}	I _C = 5.0 mA	16			V
BV_{EBO}	I _E = 100 μA	4.0			V
I_{CES}	V _{CE} = 15 V			100	μA
h_{FE}	V _{CE} = 10 V I _C = 50 mA	30		200	---
C_{OB}	V _{CB} = 15 V f = 1.0 MHz		1.8	2.5	pF
P_G	V _{CE} = 12.5 V P _{OUT} = 0.75 W f = 870 MHz	8.0	10		dB
η_C		55	60		%

